

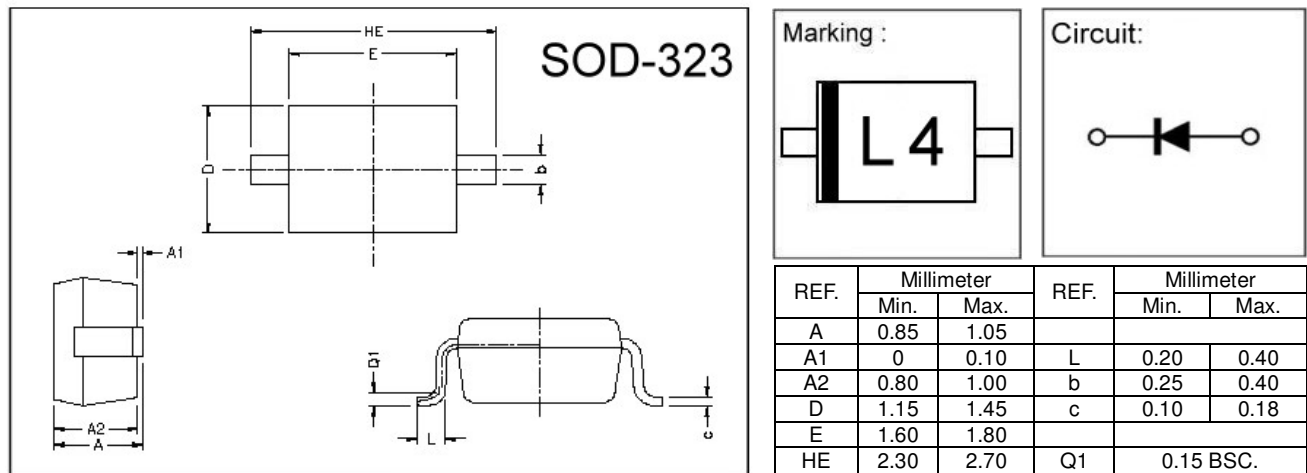
GDBAT54

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 30V, CURRENT 200mA

Description

The GDBAT54 is designed for high speed switching applications circuit protection, and voltage clamping.

Package Dimensions



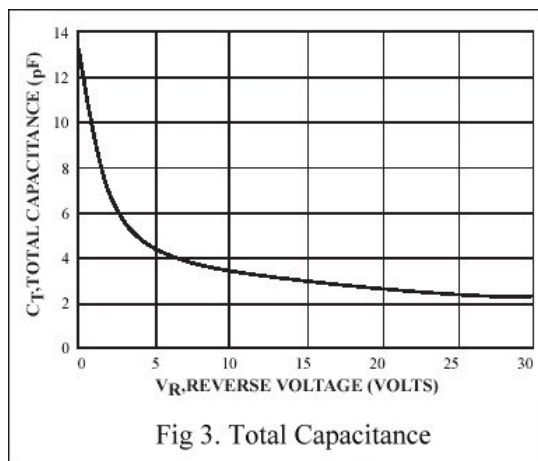
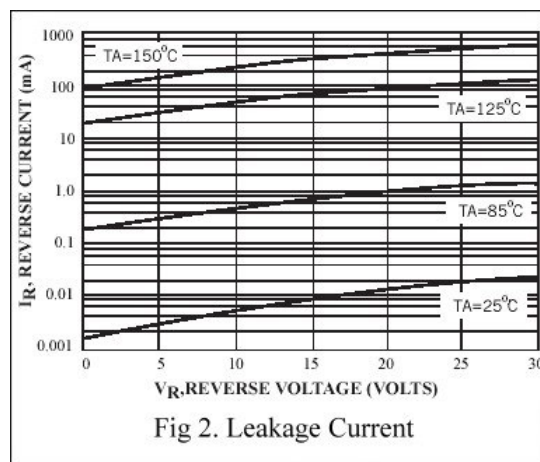
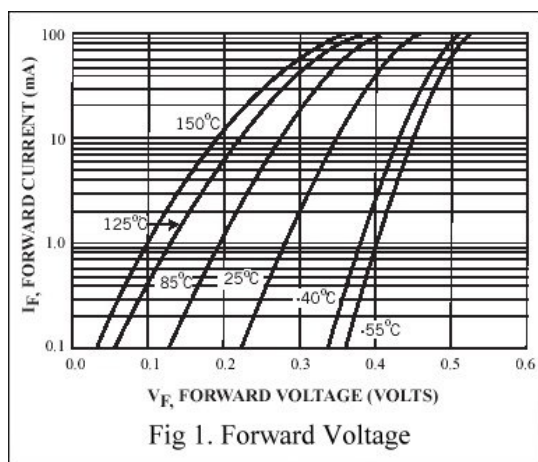
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	-55 ~ +125	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Peak Repetitive Reverse Voltage	VR	30	V
Forward Continuous Current	IF	200	mA
Peak Repetitive Forward Current	IFRM	300	mA
Surge Forward Current(t ≤ 1.0s)	IFSM	600	mA
Total Power Dissipation at Ta = 25°C	PD	225	mW

Characteristics at Ta = 25°C

characteristics	Symbol	Min	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)R	30	-	V	IR=10μA
Forward Voltage	VF(1)	-	240	mV	IF=0.1mA
	VF(2)	-	320	mV	IF=1mA
	VF(3)	-	400	mV	IF=10mA
	VF(4)	-	500	mV	IF=30mA
	VF(5)	-	1000	mV	IF=100mA
Reverse Leakage Current	IR	-	2.0	μA	VR=25V
Total Capacitance	CT	-	10	pF	VR=1V, f=1MHz
Reverse Recover Time	Trr	-	5	ns	IF=IR=10mA, IR(Rec)=1mA

Characteristics Curve

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